

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of claims:

1-6 (Canceled)

7. (Currently Amended) A semiconductor device comprising:
- an emitter region provided in a semiconductor substrate facing its principal plane,
 - a body region provided below the emitter region,
 - a drift region provided below the body region,
 - a gate electrode of trench structure, insulated from each of the emitter region, the body region, and the drift region,
 - a field region provided in the semiconductor substrate facing its ~~principle~~ principal plane, the field region being configured to divide the emitter region and the body region into cells, and
 - a contact electrode provided outside of the semiconductor substrate connecting with the emitter region and the field region,
- wherein the emitter region, the body region, and the drift region constitute an insulated gate transistor divided by the field region,
- the field region is the same conductive type as a portion of the emitter region that contacts with the field region, the field region being low in impurity concentration, ~~and~~
- the field region contacts with the contact electrode at a corner portion of contacting portion of the semiconductor substrate to the contact electrode, and
- the emitter region contacts with the contact electrode at ~~the other~~ another portion than the contacting portion of the field region to the contact electrode within ~~of the~~ contacting portion of the semiconductor substrate to the contact electrode.

8. (Currently Amended) A semiconductor device of claim 7,

wherein a plurality of ~~active devices~~ insulated gate transistors are discretely arranged in the semiconductor substrate, and each ~~active device~~ insulated gate transistor has a contacting portion to a contact electrode, and

a corner portion of a contacting portion of an ~~active device~~ insulated gate transistor positioned at the end and at opposite side to another ~~active device~~ insulated gate transistor is formed with a curved line or with an obtuse angle.

9. (Currently Amended) A semiconductor device of claim 7,
wherein the shape of contacting portion of the ~~active device~~ insulated gate transistor to the contact electrode is formed in a broader width in an end portion than in the central portion.

10. (Currently Amended) A semiconductor device of claim 9,
wherein a plurality of ~~active devices~~ insulated gate transistors are discretely arranged in the semiconductor substrate, and each ~~active device~~ insulated gate transistor has a contacting portion to a contact electrode,
an end portion of a contacting portion of an ~~active device~~ insulated gate transistor positioned at an end and at opposite side of another ~~active device~~ insulated gate transistor is formed broader than the central portion of the contacting portion, and
a corner portion of the end portion is formed with a curved line or with an obtuse angle.

11. (Currently Amended) A semiconductor device comprising:
an emitter region provided in a semiconductor substrate facing its principal plane,
a body region provided below the emitter region,
a drift region provided below the body region,
a gate electrode of trench structure, insulated from each of the emitter region, the body region, and the drift region,
a field region provided in the semiconductor substrate facing its principle plane, the field region being configured to divide the emitter region and the body region

into cells, and

a contact electrode provided outside of the semiconductor substrate conducting with the emitter region, the contact electrode having a corner portion,

wherein the emitter region, the body region, and the drift region constitute an insulated gate transistor divided by the field region,

the field region is the same conductive type as a portion of the emitter region that contacts with the field region, the field region being low in impurity concentration, and

a corner portion of a contacting portion of the emitter region mating with the corner portion of the contact electrode has an impurity concentration that is lower at the corner portion of the contacting portion than in other portions of the contacting portion.

12. (Currently Amended) A semiconductor device of claim 11,

wherein a plurality of ~~active devices~~ insulated gate transistors are discretely arranged in the semiconductor substrate, and each ~~active device~~ insulated gate transistor has a contacting portion to a contact electrode, and

a corner portion of a contacting portion of an ~~active device~~ insulated gate transistor positioned at an end and at opposite side of another ~~active device~~ insulated gate transistor is lower in impurity concentration than other portion of the contacting portion.